

General Description

The CMSA030N06L4 uses advanced SGT technology to provide excellent RDS(ON). This is suitable device for Synchronous Rectification For Server and general purpose applications.

Features

- Low On-Resistance
- 100% avalanche tested
- Small Footprint (5x6 mm) for Compact Design
- RoHS Compliant

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	65	V
V_{GS}	Gate-Source Voltage	±20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current	120	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current	84	A
I_{DM}	Pulsed Drain Current	480	A
EAS	Single Pulse Avalanche Energy ¹	450	mJ
$P_D@T_C=25^{\circ}C$	Total Power Dissipation	85	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient(min. footprint)	---	56	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-case	---	1.47	°C/W

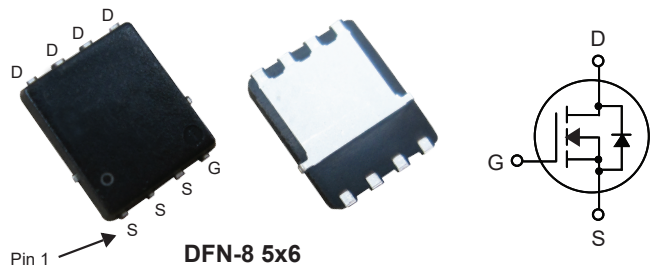
Product Summary

BVDSS	R _{DS(on)} max.	ID
65V	3mΩ	120A

Applications

- Battery management
- High Frequency Switching and Synchronous Rectification

DFN-8 5x6 Pin Configuration



Type	Package	Marking
CMSA030N06L4	DFN-8 5x6	CMSA030N06L4

Electrical Characteristics($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	65	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=50A$	---	2.5	3.0	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	2.0	---	4.0	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=60V$, $V_{GS}=0V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	±100	nA
g_{fs}	Forward Transconductance	$V_{DS}=10V$, $I_D=20A$	---	17	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	4.0	---	Ω
Q_g	Total Gate Charge	$I_D=50A$	---	48	---	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=30V$	---	17.5	---	
Q_{gd}	Gate-Drain Charge	$V_{GS}=10V$ (Note 2)	---	7	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DS}=30V$	---	13	---	ns
T_r	Rise Time	$V_{GS}=10V$	---	49	---	
$T_{d(off)}$	Turn-Off Delay Time	$R_{G_ext}=2.7\Omega$	---	44	---	
T_f	Fall Time	$I_D=50A$ (Note 2)	---	35	---	
C_{iss}	Input Capacitance	$V_{DS}=30V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	3100	---	pF
C_{oss}	Output Capacitance		---	1200	---	
C_{rss}	Reverse Transfer Capacitance		---	40	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	120	A
I_{SM}	Pulsed Source Current		---	---	480	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=50A$, $T_J=25^{\circ}\text{C}$	---	0.87	1.4	V
t_{rr}	Reverse Recovery Time	$di/dt=100A/\mu s$	---	43.4	---	ns
Q_{rr}	Reverse Recovery Charge	$T_J=25^{\circ}\text{C}$, $I_F=50A$ (Note 2)	---	37	---	nC

Note :

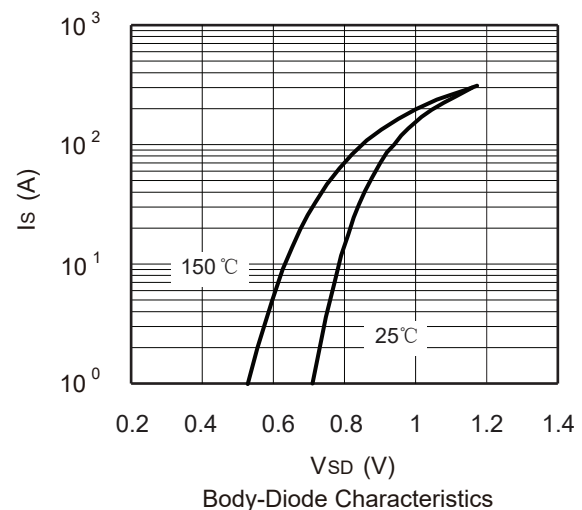
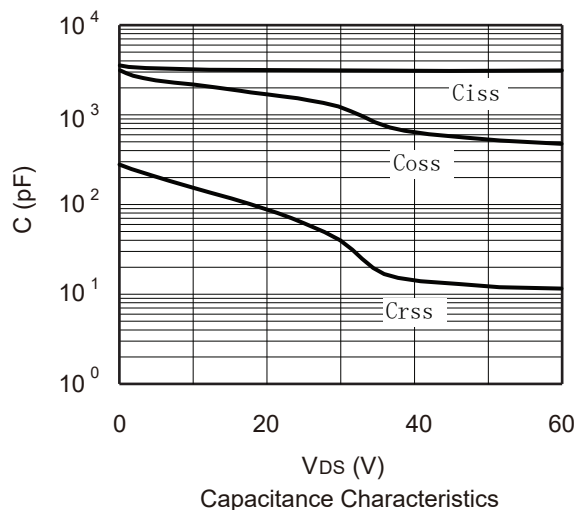
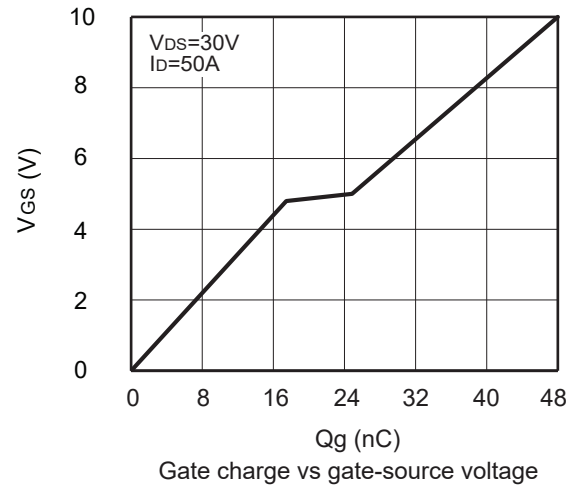
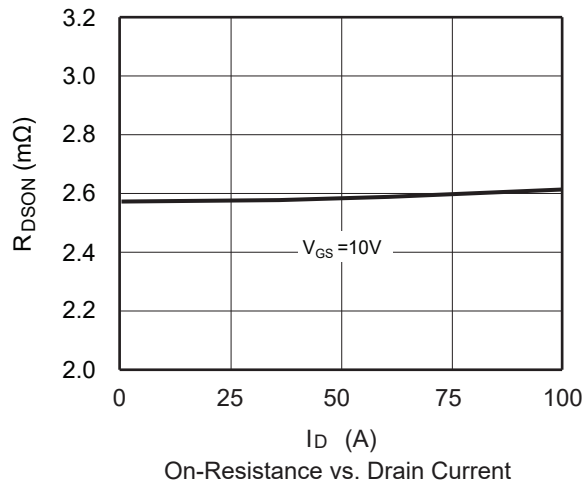
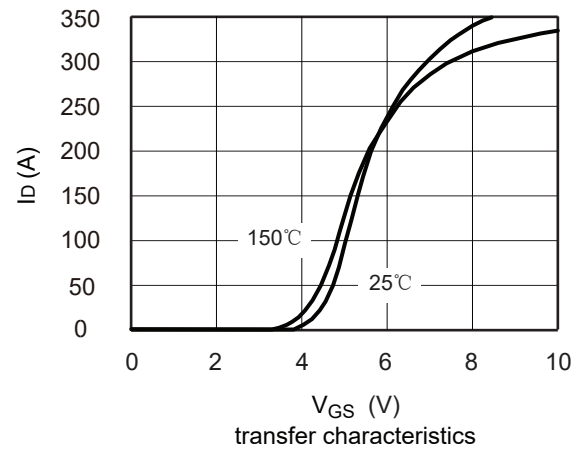
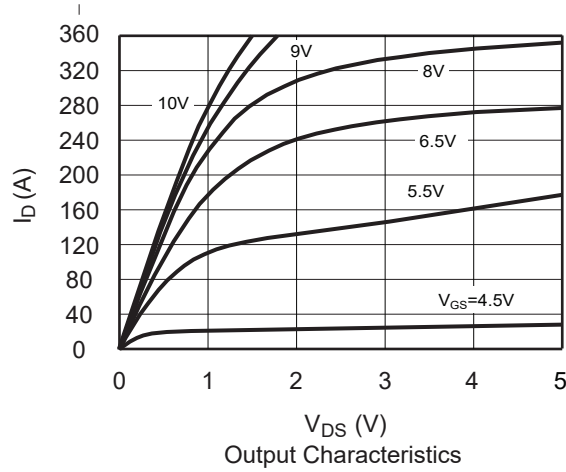
- 1.The EAS data shows Max. rating . The test condition is $V_{DD}=40V$, $V_{GS}=10V$, $L=1mH$, $I_{AS}=30A$.
- 2.Guaranteed by design, not subject to production testing.

This product has been designed and qualified for the consumer market.

Cmos assumes no liability for customers' product design or applications.

Cmos reserves the right to improve product design, functions and reliability without notice. Please refer to the latest version of specification.

Typical Characteristics



Typical Characteristics

